

(Japanese Pat. Appln. No. 264225/1997)
(Translation)
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Document: Application for Patent
Reference Number: 33409418
Date: 29th September 1997
To: Commissioner of Patent Office
International Class: H01S 3/18
Title of the Invention: SEMICONDUCTOR LAYER FORMED BY
SELECTIVE DEPOSITION AND METHOD
FOR DEPOSITING THE SAME, NITRIDE-
BASED SEMICONDUCTOR LAYER FORMED
BY SELECTIVE DEPOSITION AND METHOD
FOR DEPOSITING THE SAME, NITRIDE-
BASED SEMICONDUCTOR LIGHT
EMITTING DEVICE AND METHOD FOR
FORMING THE SAME
Number of Claims: 18
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Indication of Official Fee

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List of Attached Documents

specification: 1 copy

drawings: 1 copy

abstract: 1 copy

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Proof Required